



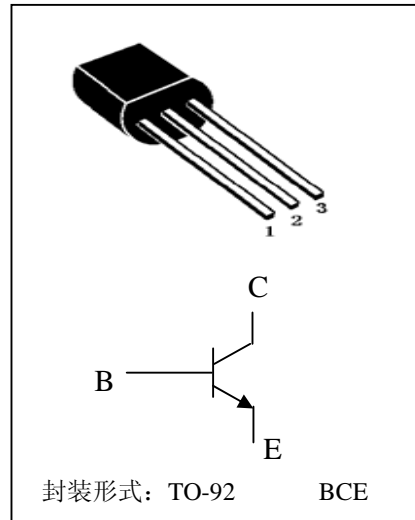
NPN高压开关晶体管/NPN High Voltage Switching Transistor

- 特点: ■击穿电压稳定 ■开关速度快 ■安全工作区宽 ■符合ROHS规范
- FEATURES: ■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■ROHS COMPLIANT
- 应用 ■节能灯 ■电子镇流器 ■电子变压器等开关电路
- APPLICATION: ■FLUORESCENT LAMP ■ELECTRONIC BALLAST ■ELECTRONIC TRANSFORMER ECT.

●最大额定值 (TC=25°C)

●Absolute Maximum Ratings (Tc=25°C)

参数名称	PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极-基极电压 Collector-Base Voltage		VCBO	600	V
集电极-发射极电压 Collector-Emitter Voltage		VCEO	410	V
发射极-基极 Emitter-Base Voltage		VEBO	9	V
集电极电流 Collector Current		Ic	0.8	A
集电极耗散功率 Total Power Dissipation		PC	12	W
最高工作温度 Junction Temperature		Tj	150	°C
贮存温度 Storage Temperature		TsTg	-55-150	°C



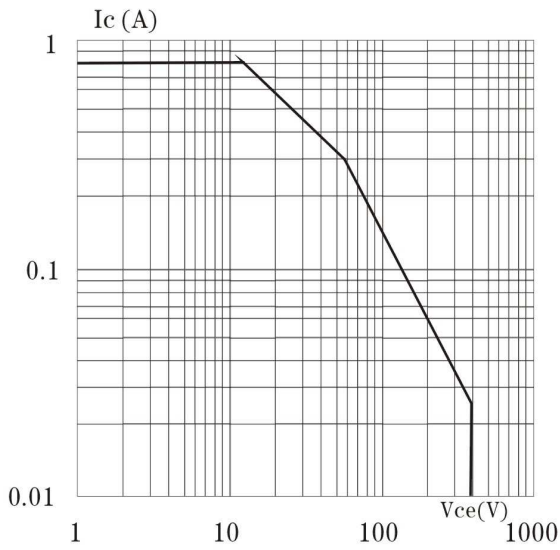
电特性 (TC=25°C)

Electrical Characteristics (Tc=25°C)

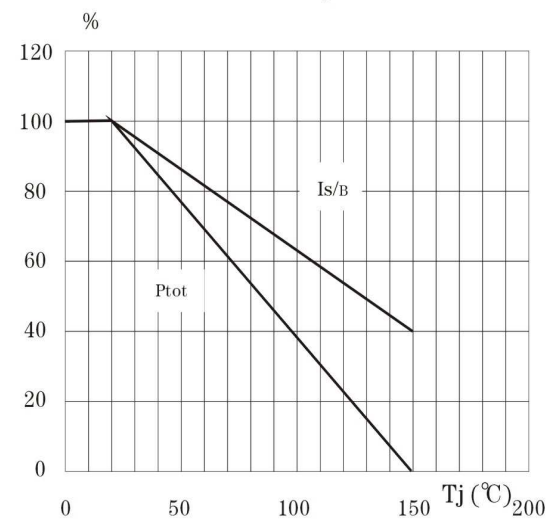
参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	ICBO	VCB=600V		5	uA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	ICEO	VCE=400V, IB=0		10	uA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	IC=10mA, IB=0	410		V
发射极-基极电压 Collector-Base Voltage	VEBO	IE=1mA, IC=0	9		V
集电极-发射极饱和压降 Collector-Emitter Saturation Voltage	Vcesat	IC=100mA, IB=20mA		0.3	
		IC=500mA, IB=100mA		0.5	V
		IC=800mA, IB=200mA		0.85	V
发射极-基极饱和压降 Base-Emitter Saturation Voltage	Vbesat	IC=500mA, IB=100mA		1.2	V
电流放大倍数 DC Current Gain	Hfe	VCE=5V, IC=200uA	8		
		VCE=5V, IC=200mA	15	30	
		VCE=5V, IC=800mA	6		
贮存时间 Storage Time	ts	VCC=5V IC=0.25A (UI9600)	1.5	2.5	us
下降时间 falling time	tf			0.8	



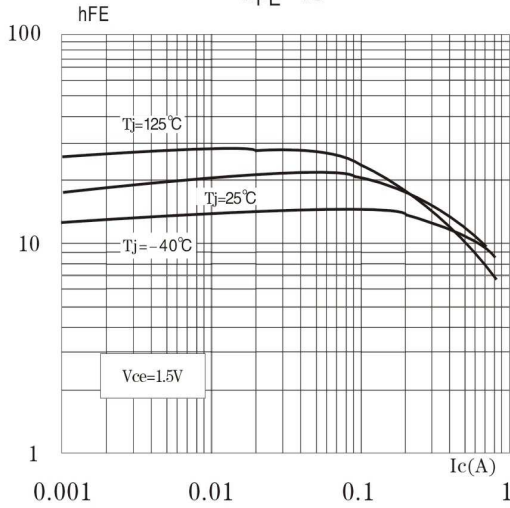
SOA(DC)



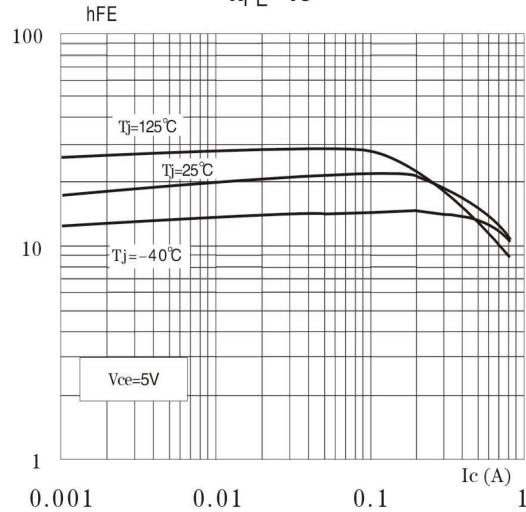
$P_c \propto T_j$



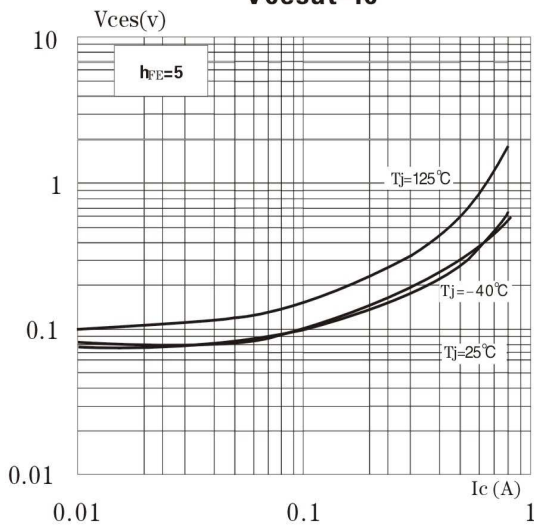
$h_{FE} - I_c$



$h_{FE} - I_c$



$V_{cesat} - I_c$



$V_{besat} - I_c$

